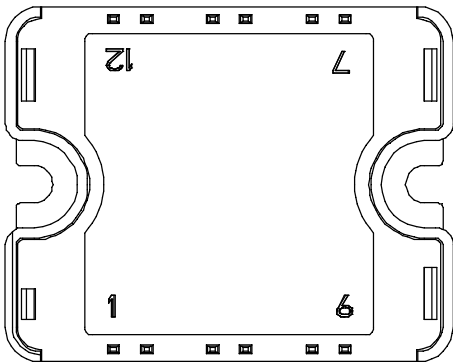
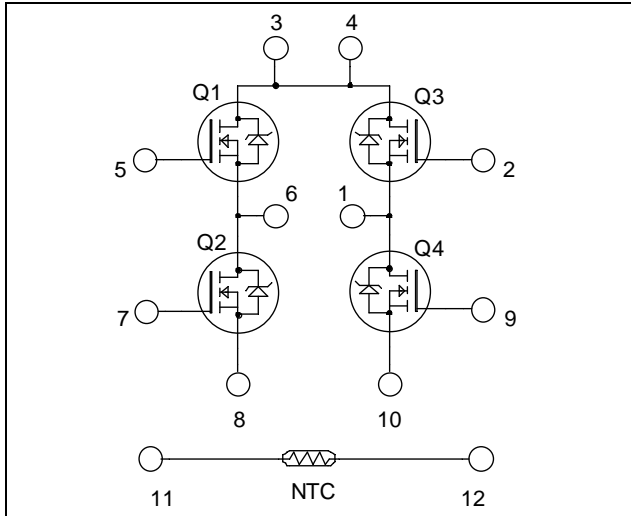


## Full - Bridge MOSFET Power Module

$V_{DSS} = 600V$   
 $R_{DSon} = 190m\Omega$  typ @  $T_j = 25^\circ C$   
 $I_D = 20A$  @  $T_c = 25^\circ C$



Pins 3/4 must be shorted together

### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features


- Power MOS 8™ FREDFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	600	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	20
		$T_c = 80^\circ C$	15
$I_{DM}$	Pulsed Drain current	125	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	230	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	208
$I_{AR}$	Avalanche current (repetitive and non repetitive)	17	A


**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$			250	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 17\text{A}$		190	230	$\text{m}\Omega$	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1\text{mA}$	3	4	5	V	
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			$\pm 100$	nA	

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		5316		$\text{pF}$
$C_{oss}$	Output Capacitance			610		
$C_{rss}$	Reverse Transfer Capacitance			56		
$Q_g$	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 300\text{V}$ $I_D = 17\text{A}$		165		nC
$Q_{gs}$	Gate – Source Charge			36		
$Q_{gd}$	Gate – Drain Charge			70		
$T_{d(on)}$	Turn-on Delay Time	<b>Resistive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 15\text{V}$ $V_{Bus} = 400\text{V}$ $I_D = 17\text{A}$ $R_G = 4.7\Omega$		37		ns
$T_r$	Rise Time			43		
$T_{d(off)}$	Turn-off Delay Time			115		
$T_f$	Fall Time			34		

**Source - Drain diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_S$	Continuous Source current (Body diode)		$T_c = 25^\circ\text{C}$			20	A
			$T_c = 80^\circ\text{C}$			15	
$V_{SD}$	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -17\text{A}$			1	V	
$dv/dt$	Peak Diode Recovery ①				30	V/ns	
$t_{rr}$	Reverse Recovery Time	$I_S = -17\text{A}$ $V_R = 100\text{V}$ $di_s/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$			200	ns
			$T_j = 125^\circ\text{C}$			370	
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		0.76	$\mu\text{C}$	
			$T_j = 125^\circ\text{C}$		1.91		

 ①  $dv/dt$  numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq -17\text{A}$     $di/dt \leq 1000\text{A}/\mu\text{s}$     $V_{DD} \leq 400\text{V}$     $T_j \leq 125^\circ\text{C}$

## Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance			0.6	°C/W	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz	4000			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight			80		g

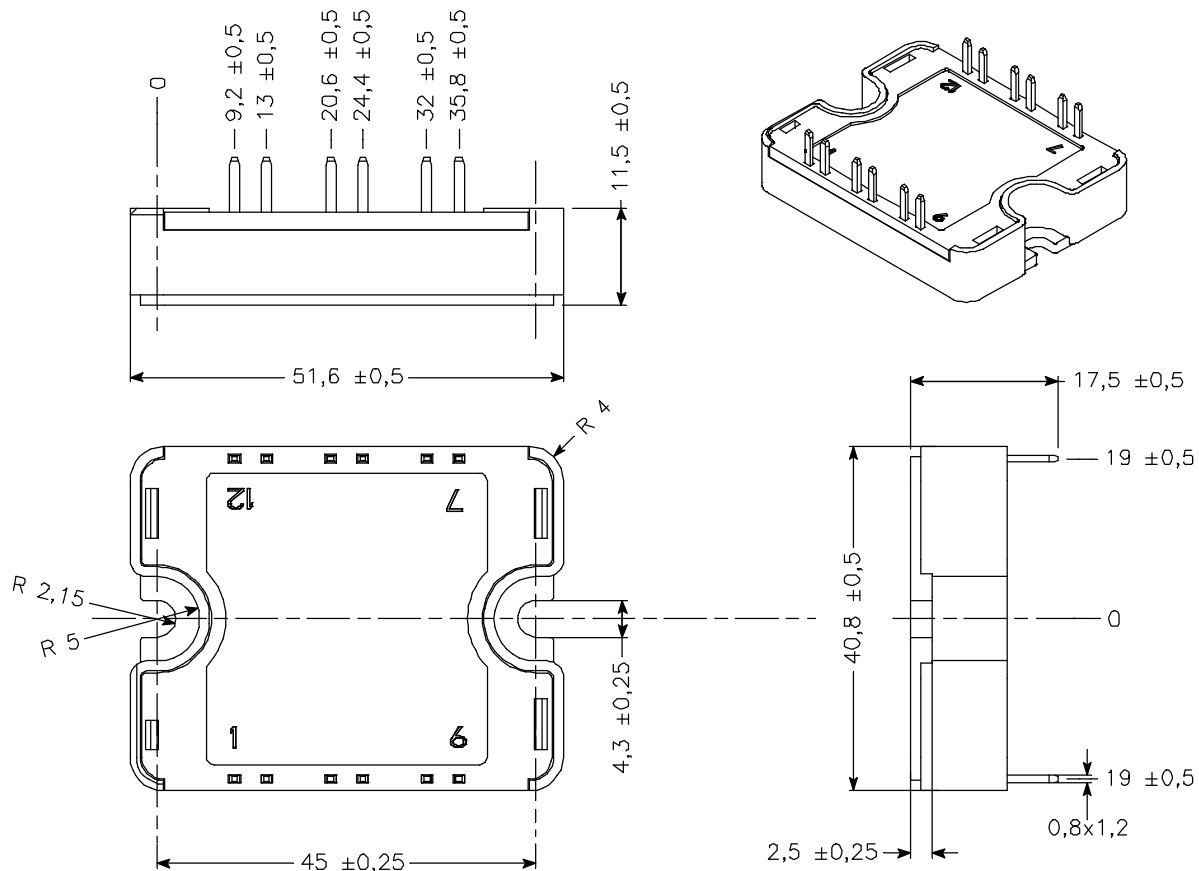
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>			5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K
ΔB/B	T <sub>C</sub> = 100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

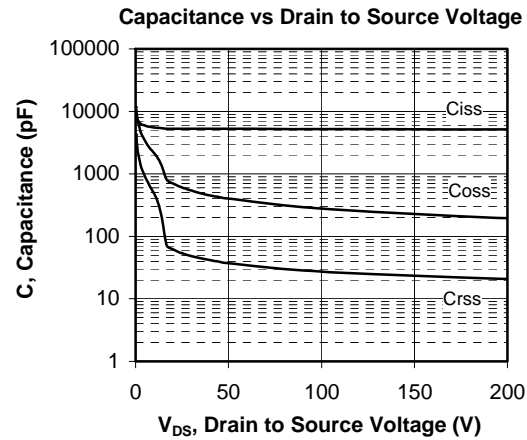
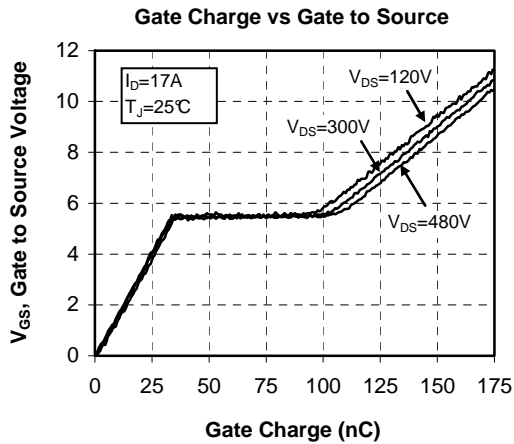
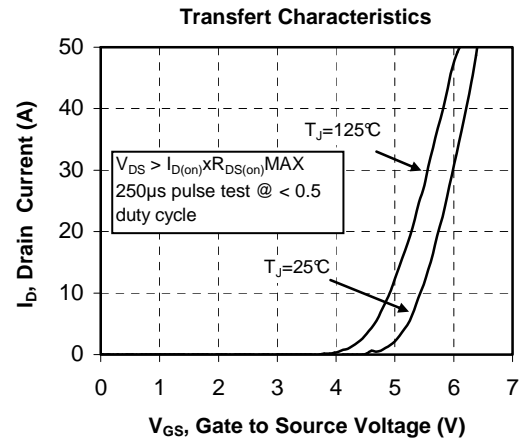
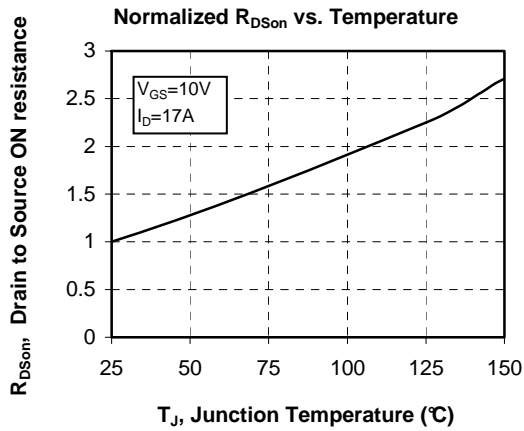
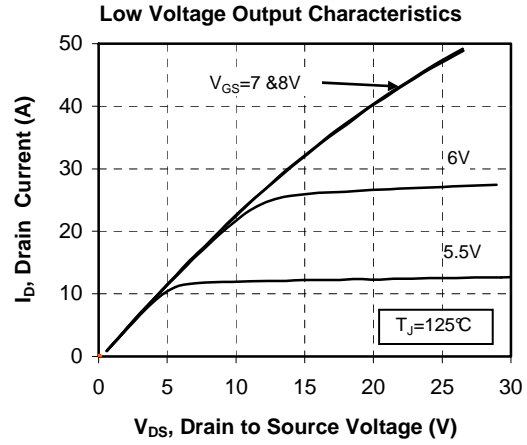
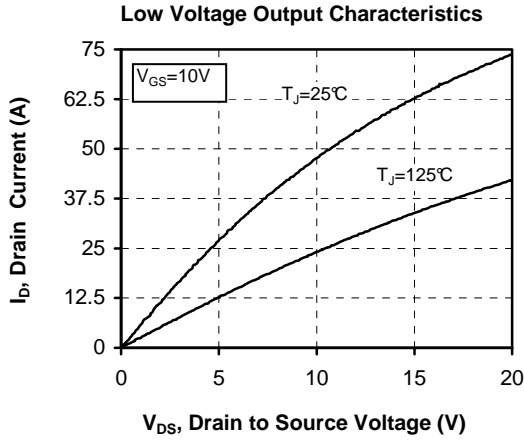
T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

## SP1 Package outline (dimensions in mm)

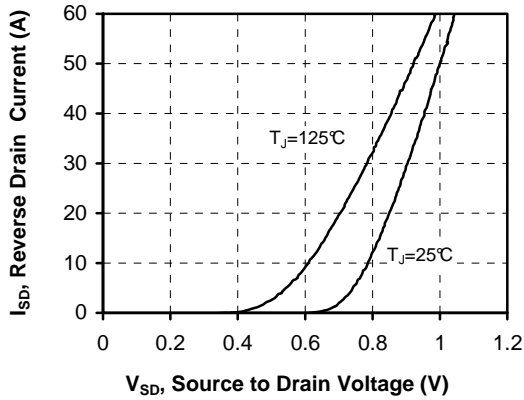


See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

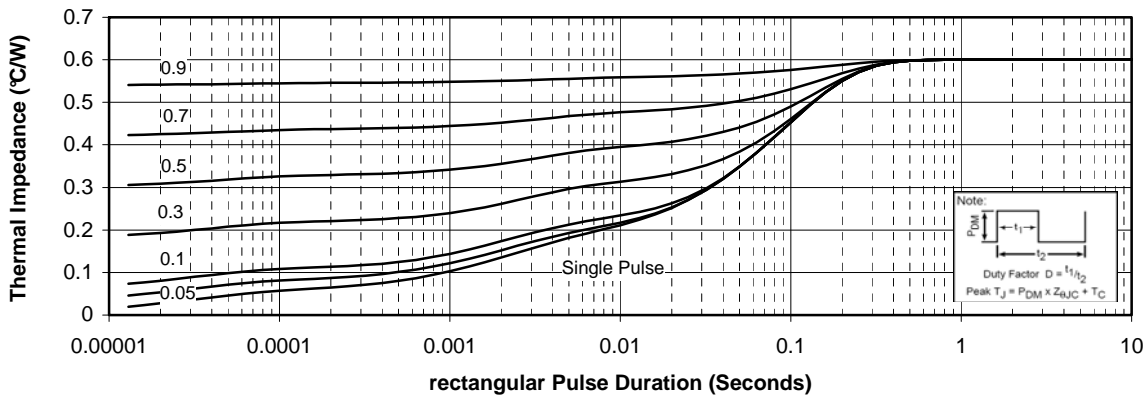
## Typical Performance Curve



Drain Current vs Source to Drain Voltage



Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.